

**Features**

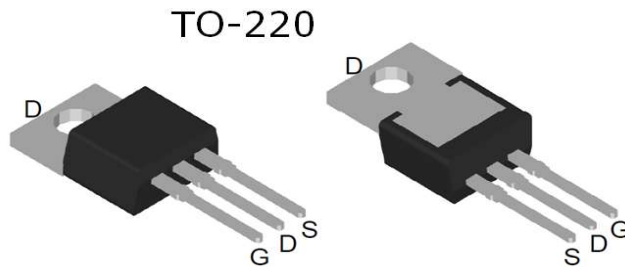
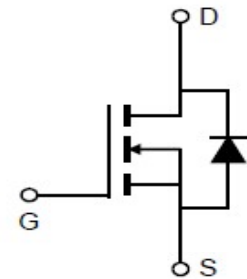
- Uses CRM(CQ) advanced SkyMOS3 technology
- Extremely low on-resistance  $R_{DS(on)}$
- Excellent  $Q_g \times R_{DS(on)}$  product(FOM)
- Qualified according to JEDEC criteria

**Applications**

- Motor control and drive
- Battery management
- UPS (Uninterruptible Power Supplies)

**Product Summary**

$V_{DS}$	200V
$R_{DS(on)}$	8.8mΩ
$I_D$	100A

**100% DVDS Tested**
**100% Avalanche Tested**

**CRST113N20NZ**

**Package Marking and Ordering Information**

Part #	Marking	Package	Packing	Reel Size	Tape Width	Qty
CRST113N20NZ	CRST113N20NZ	TO-220	Tube	N/A	N/A	50pcs

**Absolute Maximum Ratings**

Parameter	Symbol	Value	Unit
Drain-source voltage	$V_{DS}$	200	V
Continuous drain current $T_C = 25^\circ\text{C}$ (Silicon limit) $T_C = 25^\circ\text{C}$ (Package limit) $T_C = 100^\circ\text{C}$ (Silicon limit)	$I_D$	100 160 63	A
Pulsed drain current ( $T_C = 25^\circ\text{C}$ , $t_p$ limited by $T_{jmax}$ )	$I_{D\ pulse}$	400	A
Avalanche energy, single pulse ( $I_{AS} = 35\text{A}$ , $R_g=25\Omega$ )	$E_{AS}$	306	mJ
Gate-Source voltage	$V_{GS}$	$\pm 20$	V
Power dissipation ( $T_C = 25^\circ\text{C}$ )	$P_{tot}$	250	W
Operating junction and storage temperature	$T_j, T_{stg}$	-55...+150	$^\circ\text{C}$
Soldering temperature, wave soldering only allowed at leads (1.6mm from case for 10s)	$T_{sold}$	260	$^\circ\text{C}$

**Thermal Resistance**

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Thermal resistance, junction – case.	$R_{thJC}$	-	0.30	0.50	°C/W	
Thermal resistance, junction – ambient(min.)	$R_{thJA}$	-	-	62	°C/W	

**Electrical Characteristic (at  $T_j = 25\text{ °C}$ , unless otherwise specified)**

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		

**Static Characteristic**

Drain-source breakdown voltage	$BV_{DSS}$	200	-	-	V	$V_{GS}=0V, I_D=250\mu A$
Gate threshold voltage	$V_{GS(th)}$	2	3	4	V	$V_{DS}=V_{GS}, I_D=250\mu A$
Zero gate voltage drain current	$I_{DSS}$	0	-	1	$\mu A$	$V_{DS}=200V, V_{GS}=0V$ $T_j=25\text{ °C}$ $T_j=125\text{ °C}$
Gate-source leakage current	$I_{GSS}$	0	-	100	nA	$V_{GS}=\pm 20V, V_{DS}=0V$
Drain-source on-state resistance	$R_{DS(on)}$	4.0	8.8	10.7	mΩ	$V_{GS}=10V, I_D=50A$ $T_j=25\text{ °C}$
Transconductance	$g_{fs}$	40	93	180	S	$V_{DS}=5V, I_D=50A$

**Dynamic Characteristic**

Input Capacitance	$C_{iss}$	3213	4819	7229	pF	$V_{GS}=0V, V_{DS}=100V,$ $f=1MHz$
Output Capacitance	$C_{oss}$	270	405	608		
Reverse Transfer Capacitance	$C_{rss}$	15	23	46		
Gate Total Charge	$Q_G$	46	69	104	nC	$V_{GS}=10V, V_{DS}=100V,$ $I_D=50A, f=1MHz$
Gate-Source charge	$Q_{gs}$	17	25	38		
Gate-Drain charge	$Q_{gd}$	11	16	32		

Turn-on delay time	$t_{d(on)}$	11	16	24	ns	$V_{DS}=100V$ $I_D=50A$ $R_G=2.7\Omega$ $V_{GS}=10V$ ;
Rise time	$t_r$	55	82	123		
Turn-off delay time	$t_{d(off)}$	37	55	110		
Fall time	$t_f$	56	84	126		
Gate resistance	$R_G$	2.3	4.2	6.0	Ω	$V_{GS}=0V, V_{DS}=0V,$ $f=1MHz$

**Body Diode Characteristic**

Parameter	Symbol	Value			Unit	Test Condition
		min.	typ.	max.		
Body Diode Forward Voltage	$V_{SD}$	0.5	0.85	1.4	V	$V_{GS}=0V, I_{SD}=50A$
Body Diode Continuous Forward Current	$I_S$	-	-	100	A	$T_C = 25^\circ C$
Body Diode Pulsed Current	$I_{S\ pulse}$	-	-	400	A	$T_C = 25^\circ C$
Body Diode Reverse Recovery Time	$t_{rr}$	65	129	258	ns	$I_{SD}=50A, V_{GS}=0V,$ $dI/dt=100A/us$ ;
Body Diode Reverse Recovery Charge	$Q_{rr}$	376	752	1504	nC	

Typical Performance Characteristics

Fig 1: Output Characteristics

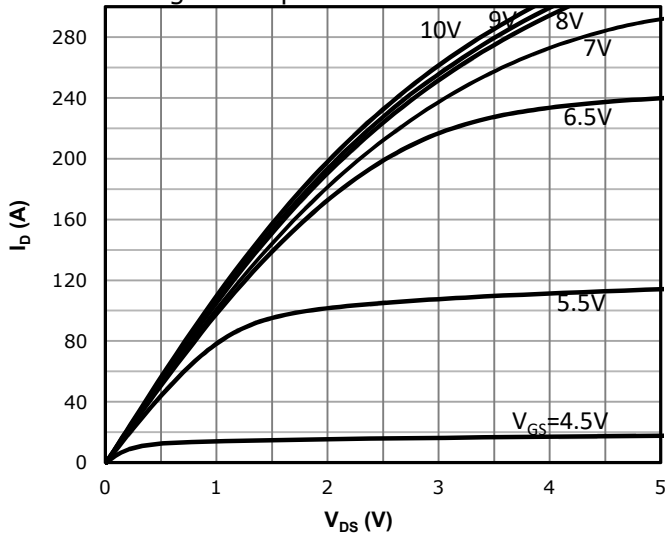


Fig 2: Transfer Characteristics

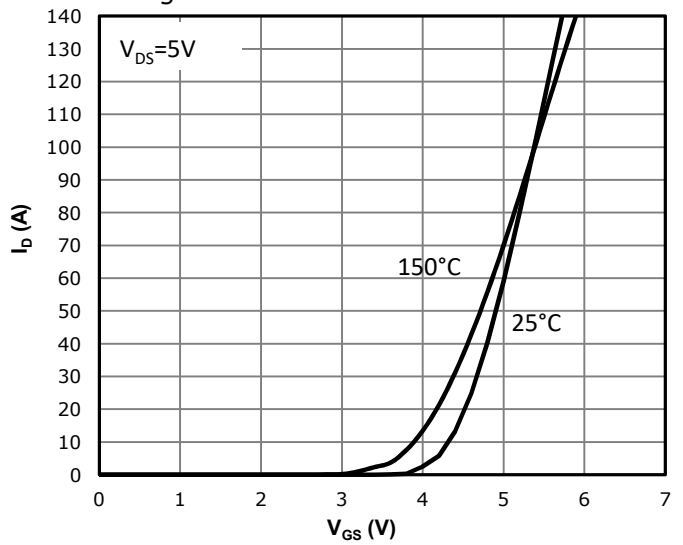


Fig 3: Rds(on) vs Drain Current and Gate Voltage

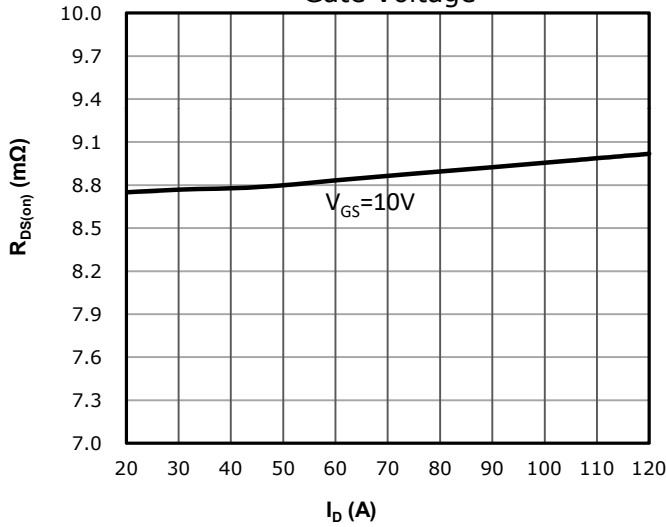


Fig 4: Rds(on) vs Gate Voltage

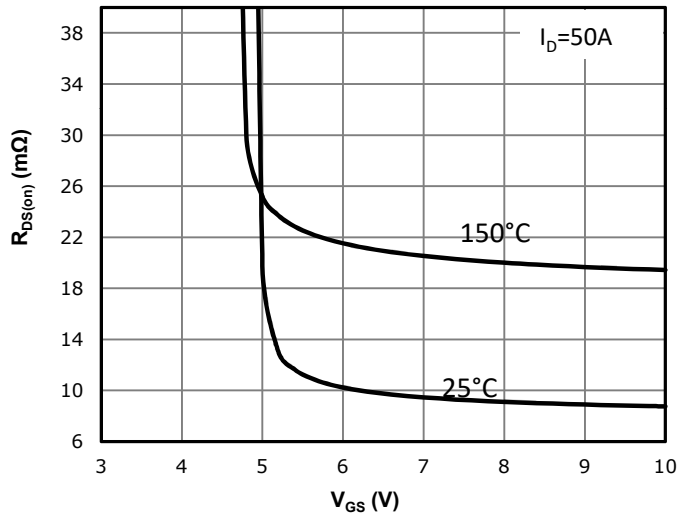


Fig 5: Rds(on) vs. Temperature

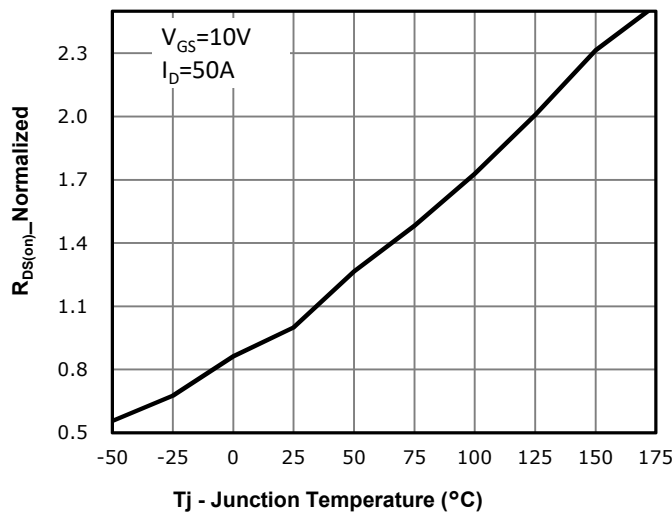


Fig 6: Capacitance Characteristics

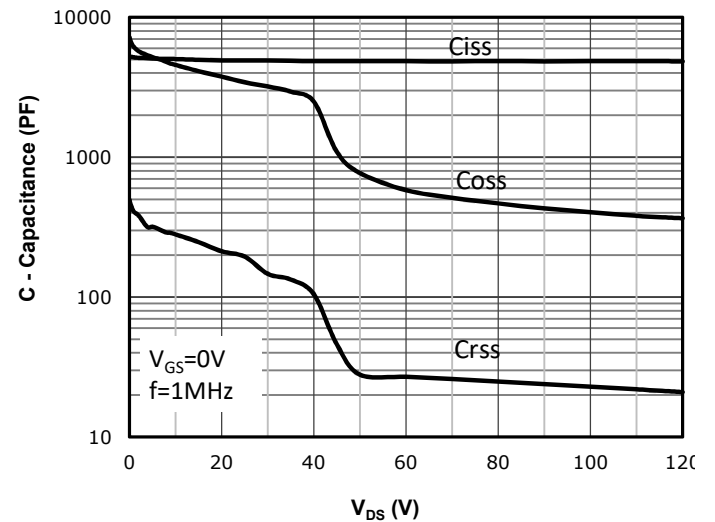


Fig 7: Vgs(th) vs. Temperature

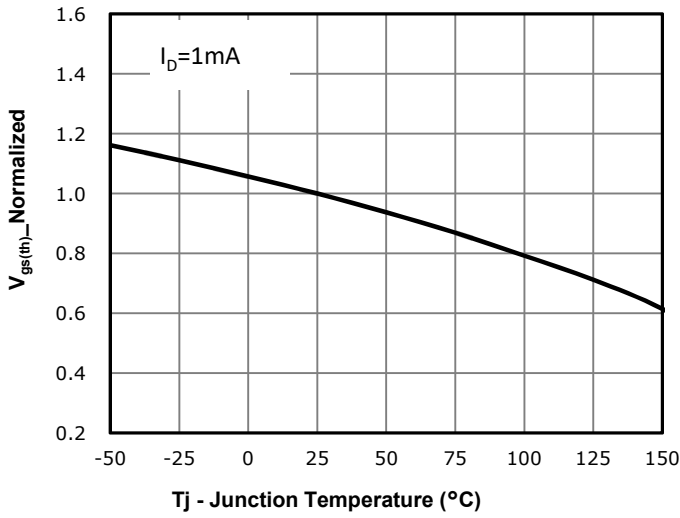


Fig 8: BVdss vs. Temperature

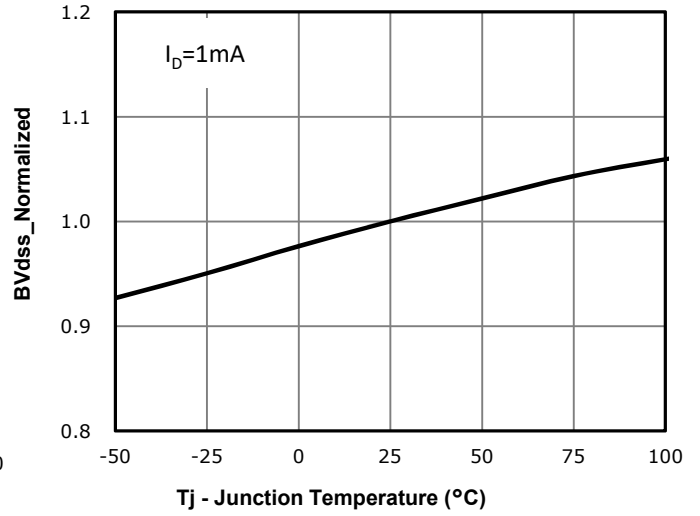


Fig 9: Gate Charge Characteristics

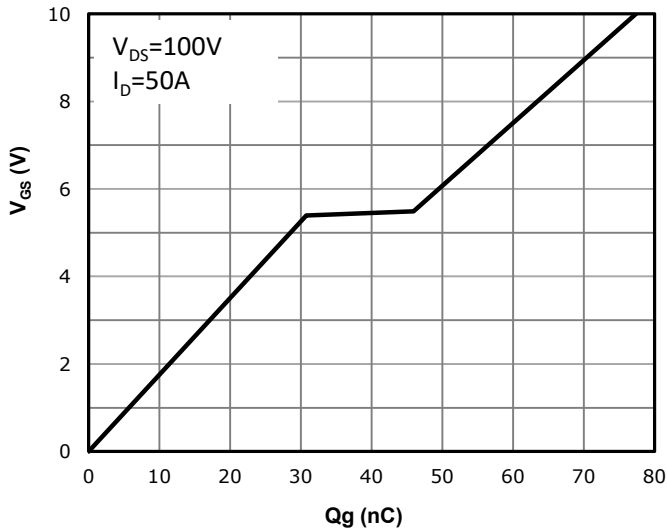


Fig 10: Body-diode Forward Characteristics

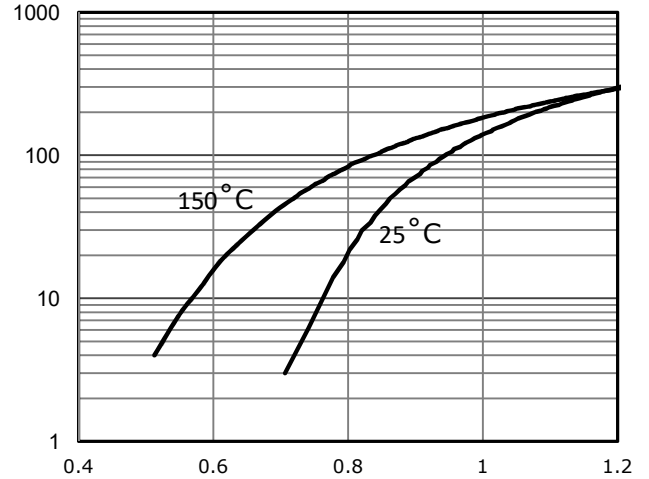


Fig 11: Power Dissipation

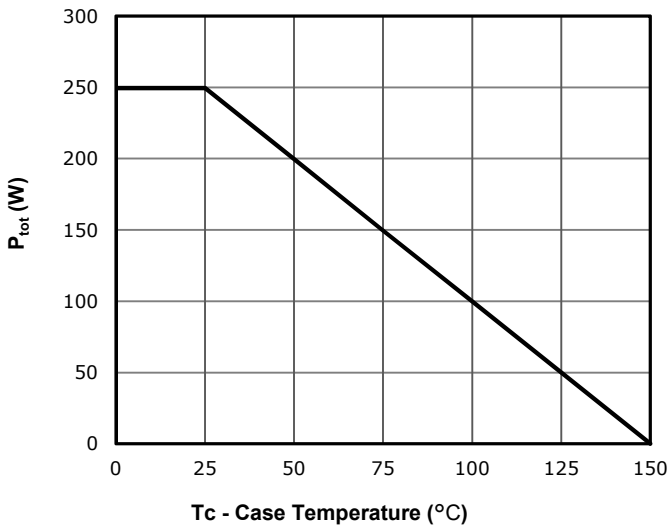


Fig 12: Drain Current Derating

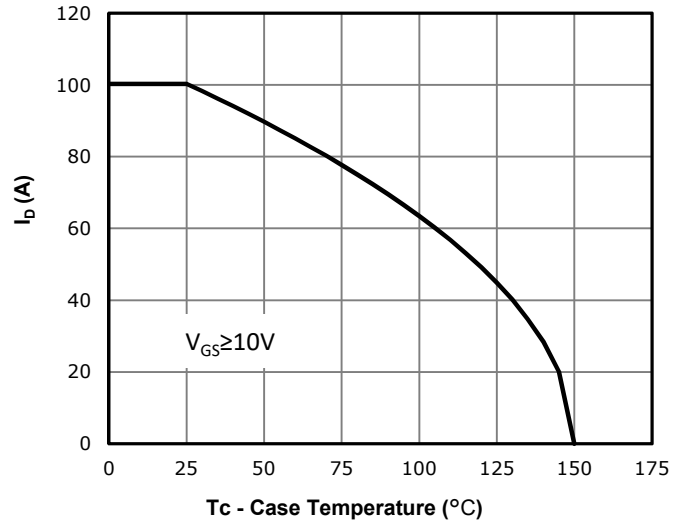


Fig 13: Safe Operating Area

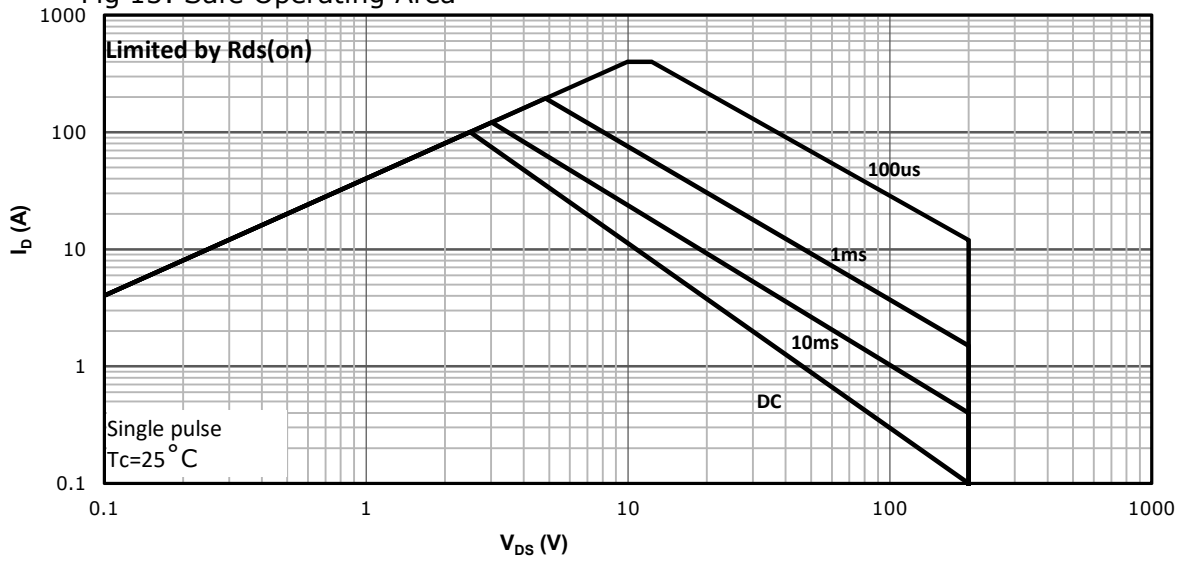
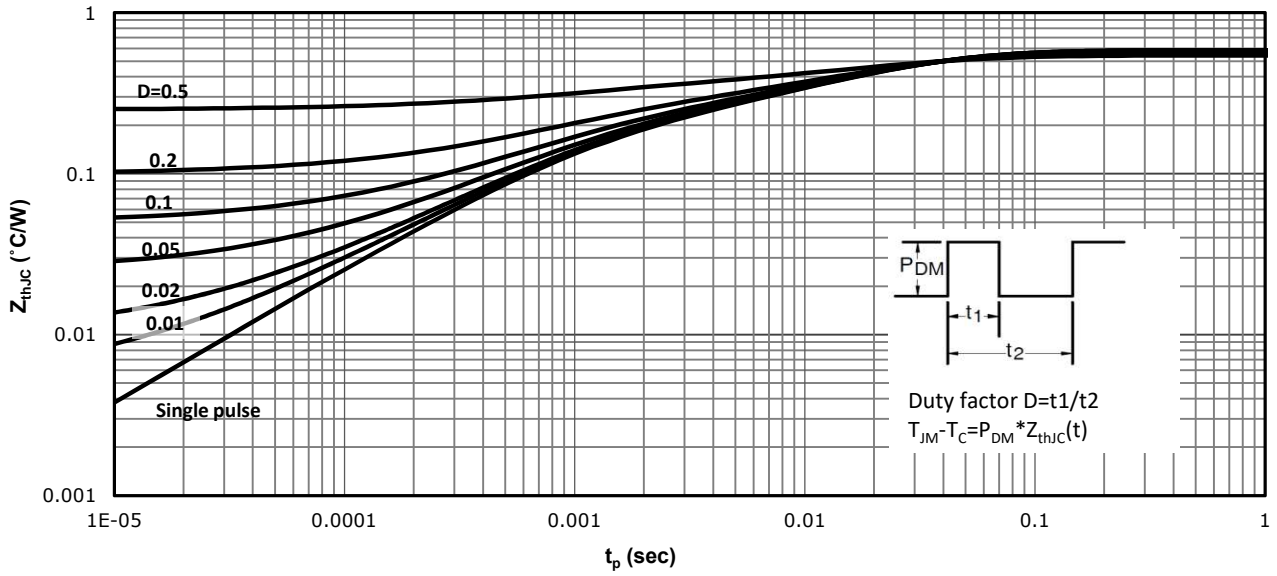
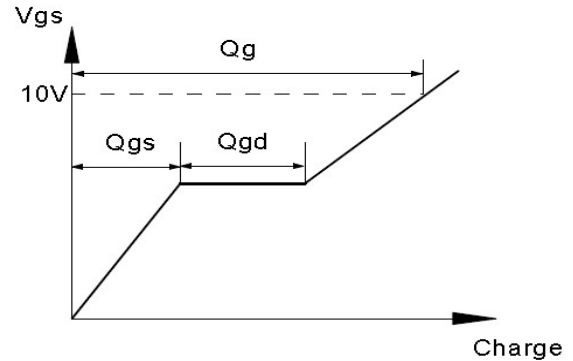
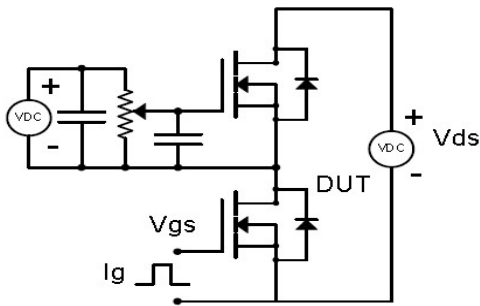


Fig 12: Max. Transient Thermal Impedance

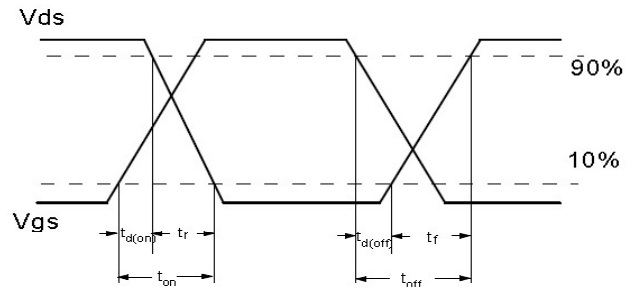
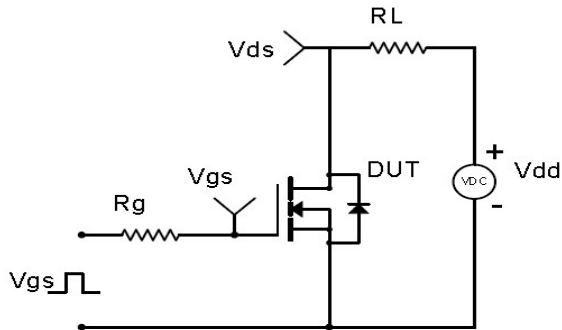


**Test Circuit & Waveform**

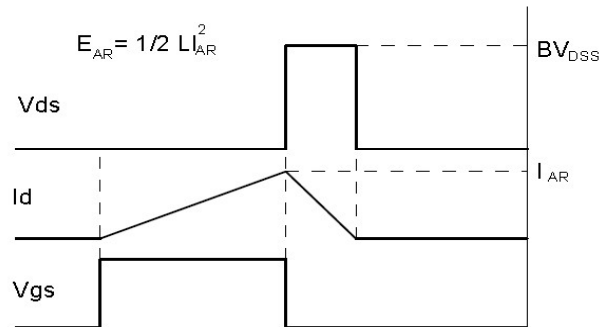
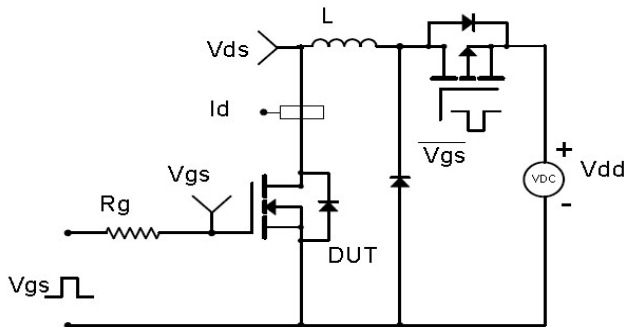
Gate Charge Test Circuit & Waveform



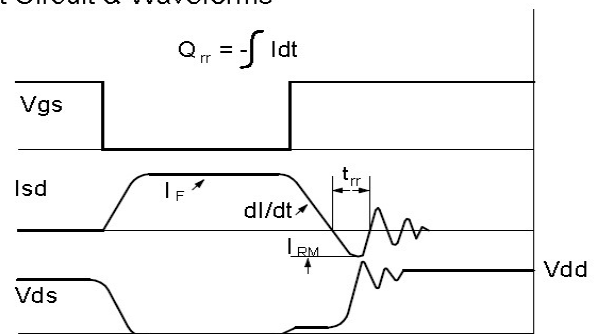
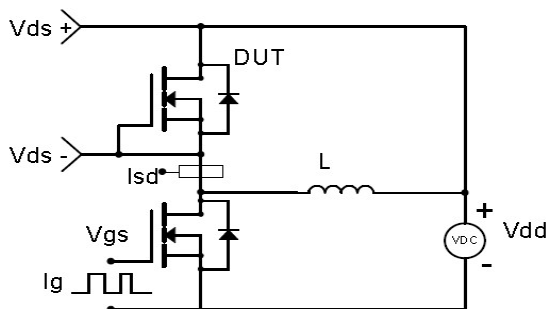
Resistive Switching Test Circuit & Waveforms



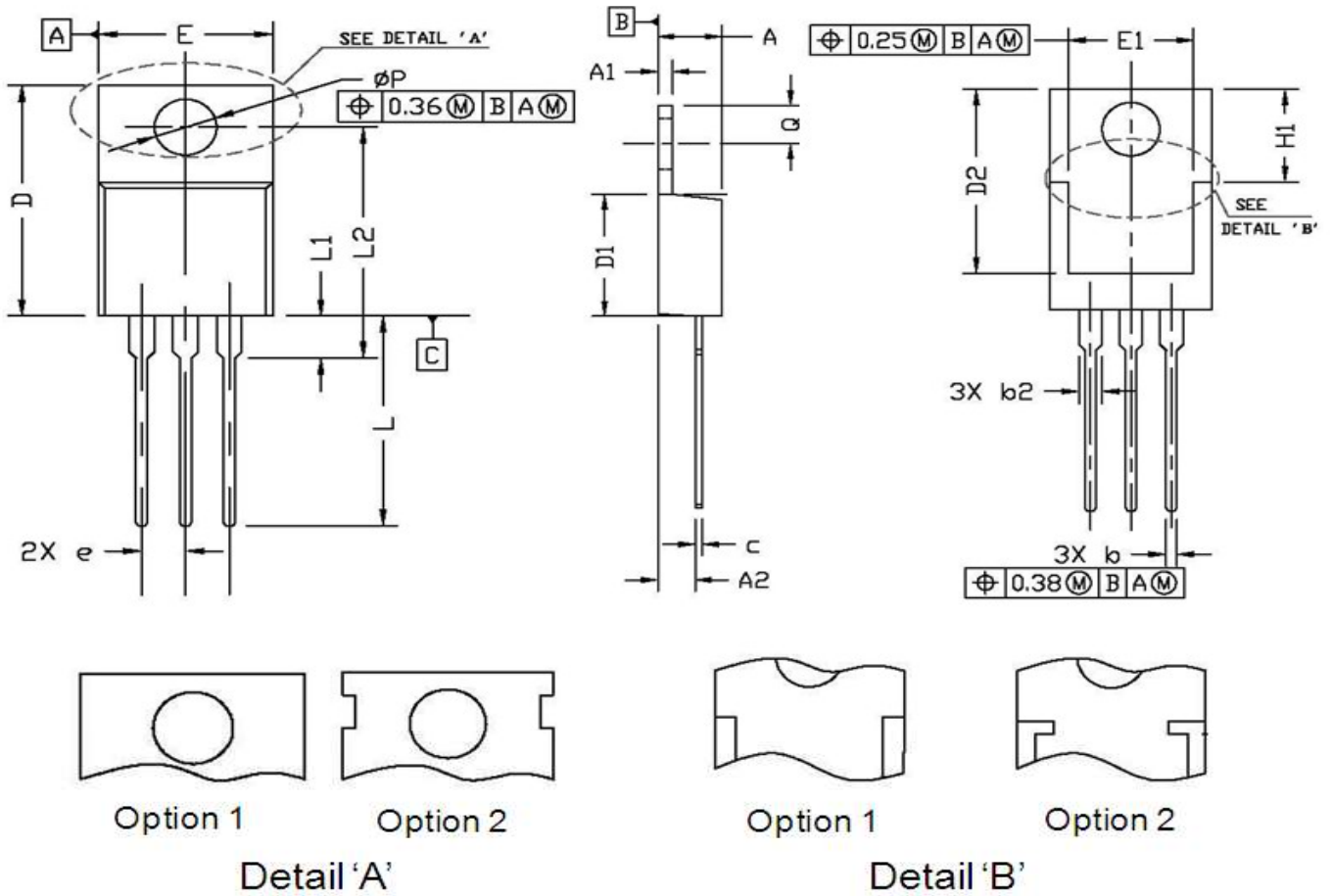
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms





**Package Outline: TO-220-3L**


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.42	4.72	0.174	0.186
A1	1.20	1.40	0.047	0.055
A2	2.35	2.90	0.093	0.114
b	0.71	0.91	0.028	0.036
b2	1.20	1.38	0.047	0.054
c	0.45	0.60	0.018	0.024
D	14.70	16.00	0.579	0.630
D1	8.80	9.50	0.346	0.374
D2	11.75	13.60	0.463	0.535
e	2.54 BSC.		0.100 BSC.	
E	9.70	10.40	0.382	0.409
E1	7.00	8.90	0.276	0.350
H1	6.10	6.50	0.240	0.256
L	12.80	14.80	0.504	0.583
L1	2.50	3.90	0.098	0.154
L2	12.13	16.50	0.478	0.650
Q	2.60	3.00	0.102	0.118
P	3.60	3.95	0.142	0.156

## Marking



**NOTE:**

NXBBAAAAY

- N —Wire Bond code
- X —Assembly location code
- BB —Fab code
- AAAA —Lot code
- Y —Bin code

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**Revision History**

Revision	Date	Major changes
1.0	2022/8/31	Release of formal version.

**Disclaimer**

Unless otherwise specified in the datasheet, the product is designed and qualified as a standard commercial product and is not intended for use in applications that require extraordinary levels of quality and reliability, such as automotive, aviation/aerospace and life-support devices or systems.

Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.

CRM(CQ) reserves the right to improve product design, function and reliability without notice.

单击下面可查看定价，库存，交付和生命周期等信息

[>>CRMICRO\(华润微\)](#)